



**MJ802**

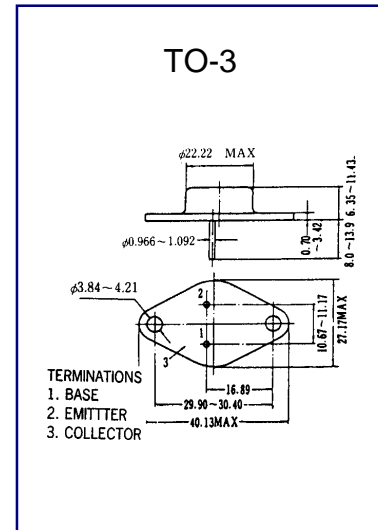
**NPN PLANAR SILICON TRANSISTOR**

**AUDIO POWER AMPLIFIER  
DC TO DC CONVERTER**

- High Current Capability
- High Power Dissipation
- Complementary to MJ4502

**ABSOLUTE MAXIMUM RATING (Ta=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	100	V
Collector-Emitter Voltage	VCEO	90	V
Emitter-Base voltage	VEBO	4	V
Collector Current (DC)	IC	30	A
Collector Dissipation	PC	200	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-50~150	°C



**ELECTRICAL CHARACTERISTICS (Ta=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BVCBO	IC=10 mA IE=0	100			V
Collector Emitter Breakdown Voltage	BVCEO	IC=5 mA RBE=	90			V
Emitter Base Breakdown Voltage	BVEBO	IE=5 mA IC=0	4			V
Collector Cutoff Current	ICBO	VCB=50V IE=0			0.1	mA
Emitter Cutoff Current	IEBO	VEB=4V IC=0			0.1	mA
*DC Current Gain	hFE1	VCE=5V IC=7.5A	25		100	
DC Current Gain	hFE2	VCE=5V IC=15A	20			
Collector- Emitter Saturation Voltage	VCE(sat)	IC=7.5A IB=0.75A			0.8	V